

TLV910x-Q1 Automotive 16V, 1MHz, Rail-to-Rail Input/Output, Low Power Op Amp

1 Features

- AEC-Q100 qualified for automotive applications
 - Temperature grade 1: -40°C to $+125^{\circ}\text{C}$, T_A
- Rail-to-rail input and output
- Wide bandwidth: 1.1MHz GBW
- Low quiescent current: 120 μA per amplifier
- Low offset voltage: $\pm 300\mu\text{V}$
- Low offset voltage drift: $\pm 0.6\mu\text{V}/^{\circ}\text{C}$
- Low noise: 28nV/ $\sqrt{\text{Hz}}$ at 10kHz
- High common-mode rejection: 110dB
- Low bias current: $\pm 10\text{pA}$
- High slew rate: 4.5V/ μs
- Wide supply: $\pm 1.35\text{V}$ to $\pm 8\text{V}$, 2.7V to 16V
- Robust EMIRR performance: 77dB at 1.8GHz

2 Applications

- [HEV/EV battery-management system \(BMS\)](#)
- [HEV/EV OBC & DC/DC converter](#)
- [HEV/EV inverter & motor control](#)
- [Body control module \(BCM\)](#)
- [Zone control module](#)
- [Domain gateway](#)
- [12V/48V power distribution box](#)
- [Automotive HVAC compressor module](#)
- [Electric power steering \(EPS\)](#)

3 Description

The TLV910x-Q1 family (TLV9101-Q1, TLV9102-Q1, and TLV9104-Q1) is a family of 16V general purpose operational amplifiers. This family offers excellent DC precision and AC performance, including rail-to-rail input/output, low offset ($\pm 300\mu\text{V}$, typical), low offset drift ($\pm 0.6\mu\text{V}/^{\circ}\text{C}$, typical), and 1.1MHz bandwidth.

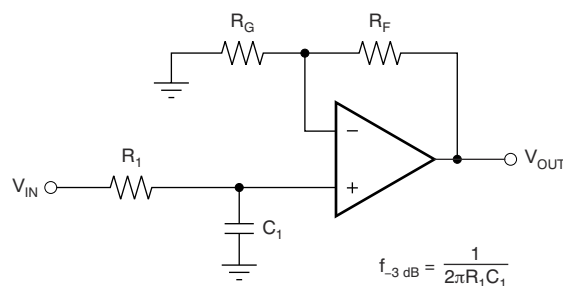
Wide differential and common-mode input-voltage range, high output current ($\pm 80\text{mA}$, typical), high slew rate (4.5V/ μs , typical), and low power operation (115 μA , typical) make the TLV910x-Q1 a robust, low-power, high-performance operational amplifier for automotive applications.

The TLV910x-Q1 family of op amps is available in several packages, and is specified from -40°C to 125°C .

Device Information

PART NUMBER ⁽¹⁾	CHANNEL COUNT	PACKAGE	PACKAGE SIZE ⁽⁴⁾
TLV9101-Q1 ⁽²⁾	Single	DBV (SOT-23, 5) ⁽³⁾	2.9mm × 2.8mm
		DCK (SC70, 5) ⁽³⁾	2mm × 2.1mm
TLV9102-Q1 ⁽²⁾	Dual	D (SOIC, 8) ⁽³⁾	4.9mm × 6mm
		DGK (VSSOP, 8) ⁽³⁾	3mm × 4.9mm
TLV9104-Q1	Quad	D (SOIC, 14) ⁽³⁾	8.65mm × 6mm
		PW (TSSOP, 14)	5mm × 6.4mm

- (1) For all available packages, see [Section 10](#).
- (2) This device is preview only.
- (3) This package is preview only.
- (4) The package size (length × width) is a nominal value and includes pins, where applicable.



$$f_{-3\text{dB}} = \frac{1}{2\pi R_1 C_1}$$

$$\frac{V_{\text{OUT}}}{V_{\text{IN}}} = \left(1 + \frac{R_F}{R_G}\right) \left(\frac{1}{1 + sR_1 C_1}\right)$$

TLV910x-Q1 in a Single-Pole, Low-Pass Filter



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4 Pin Configuration and Functions



Figure 4-1. TLV9101-Q1⁽¹⁾ DBV Package
5-Pin SOT-23
Top View

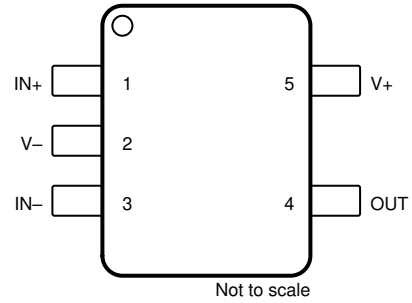
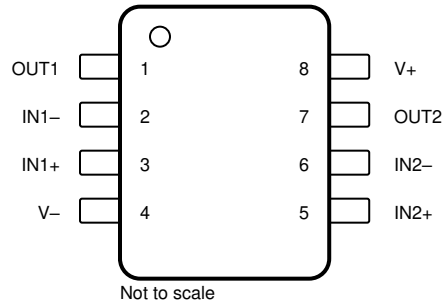


Figure 4-2. TLV9101-Q1⁽¹⁾ DCK Package
5-Pin SC70
Top View

Table 4-1. Pin Functions: TLV9101-Q1

NAME	PIN		I/O	DESCRIPTION
	DBV	DCK and DRL		
+IN	3	1	I	Noninverting input
-IN	4	3	I	Inverting input
OUT	1	4	O	Output
V+	5	5	—	Positive (highest) power supply
V-	2	2	—	Negative (lowest) power supply

1. This package is preview only.

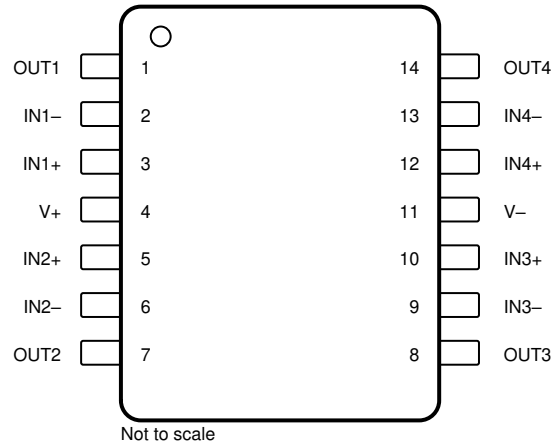


**Figure 4-3. TLV9102-Q1⁽¹⁾ D and DGK Package
8-Pin SOIC and VSSOP
Top View**

Table 4-2. Pin Functions: TLV9102-Q1

PIN		I/O	DESCRIPTION
NAME	NO.		
IN1+	3	I	Noninverting input, channel 1
IN1–	2	I	Inverting input, channel 1
IN2+	5	I	Noninverting input, channel 2
IN2–	6	I	Inverting input, channel 2
OUT1	1	O	Output, channel 1
OUT2	7	O	Output, channel 2
V+	8	—	Positive (highest) power supply
V–	4	—	Negative (lowest) power supply

1. This package is preview only.



Not to scale

**Figure 4-4. TLV9104-Q1 D⁽¹⁾ and PW Package
14-Pin SOIC⁽¹⁾ and TSSOP
Top View**

Table 4-3. Pin Functions: TLV9104-Q1

PIN		I/O	DESCRIPTION
NAME	SOIC and TSSOP		
IN1+	3	I	Noninverting input, channel 1
IN1–	2	I	Inverting input, channel 1
IN2+	5	I	Noninverting input, channel 2
IN2–	6	I	Inverting input, channel 2
IN3+	10	I	Noninverting input, channel 3
IN3–	9	I	Inverting input, channel 3
IN4+	12	I	Noninverting input, channel 4
IN4–	13	I	Inverting input, channel 4
NC	—	—	Do not connect
OUT1	1	O	Output, channel 1
OUT2	7	O	Output, channel 2
OUT3	8	O	Output, channel 3
OUT4	14	O	Output, channel 4
V+	4	—	Positive (highest) power supply
V–	11	—	Negative (lowest) power supply

1. This package is preview only.

5 Specifications

5.1 Absolute Maximum Ratings

over operating ambient temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
Supply voltage, $V_S = (V+) - (V-)$		0	20	V
Signal input pins	Common-mode voltage ⁽³⁾	$(V-) - 0.5$	$(V+) + 0.5$	V
	Differential voltage ⁽³⁾		$V_S + 0.2$	V
	Current ⁽³⁾	-10	10	mA
Shutdown pin voltage		$V-$	$V+$	V
Output short-circuit ⁽²⁾		Continuous		
Operating ambient temperature, T_A		-55	150	°C
Junction temperature, T_J			150	°C
Storage temperature, T_{stg}		-65	150	°C

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) Short-circuit to ground, one amplifier per package.
- (3) Input pins are diode-clamped to the power-supply rails. Input signals that may swing more than 0.5V beyond the supply rails must be current limited to 10mA or less.

5.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000
		Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±1000

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating ambient temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_S	Supply voltage, $(V+) - (V-)$	2.7	16	V
V_I	Input voltage range	$(V-) - 0.2$	$(V+) + 0.2$	V
T_A	Specified temperature	-40	125	°C

5.4 Thermal Information for Quad Channel

THERMAL METRIC ⁽¹⁾		TLV9104-Q1		UNIT
		D ⁽²⁾ (SOIC)	PW (TSSOP)	
		14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	105.2	134.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	61.2	55.0	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	61.1	79.0	°C/W
ψ_{JT}	Junction-to-top characterization parameter	21.4	9.2	°C/W
ψ_{JB}	Junction-to-board characterization parameter	60.7	78.1	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application note.
- (2) This package option is preview for TLV9104-Q1.

5.5 Electrical Characteristics

For $V_S = (V+) - (V-) = 2.7\text{ V to }16\text{ V}$ ($\pm 1.35\text{ V to } \pm 8\text{ V}$) at $T_A = 25^\circ\text{C}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{O\text{ UT}} = V_S / 2$, unless otherwise noted.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
OFFSET VOLTAGE							
V_{OS}	Input offset voltage	$V_{CM} = V-$			± 0.3	± 1.5	mV
			$T_A = -40^\circ\text{C to }125^\circ\text{C}$			± 1.75	
dV_{OS}/dT	Input offset voltage drift		$T_A = -40^\circ\text{C to }125^\circ\text{C}$		± 0.6		$\mu\text{V}/^\circ\text{C}$
PSRR	Input offset voltage versus power supply	$V_{CM} = V-$	$T_A = -40^\circ\text{C to }125^\circ\text{C}$		± 0.1	± 0.7	$\mu\text{V}/\text{V}$
	Channel separation	$f = 0\text{ Hz}$			5		$\mu\text{V}/\text{V}$
INPUT BIAS CURRENT							
I_B	Input bias current				± 10		pA
I_{OS}	Input offset current				± 5		pA
NOISE							
E_N	Input voltage noise	$f = 0.1\text{ Hz to }10\text{ Hz}$			6		μV_{PP}
					1		μV_{RMS}
e_N	Input voltage noise density	$f = 1\text{ kHz}$			30		$\text{nV}/\sqrt{\text{Hz}}$
		$f = 10\text{ kHz}$			28		
i_N	Input current noise	$f = 1\text{ kHz}$			2		$\text{fA}/\sqrt{\text{Hz}}$
INPUT VOLTAGE RANGE							
V_{CM}	Common-mode voltage range			$(V-) - 0.2$		$(V+) + 0.2$	V
CMRR	Common-mode rejection ratio	$V_S = 16\text{ V}, (V-) - 0.1\text{ V} < V_{CM} < (V+) - 2\text{ V}$ (Main input pair)	$T_A = -40^\circ\text{C to }125^\circ\text{C}$		90	110	dB
		$V_S = 4\text{ V}, (V-) - 0.1\text{ V} < V_{CM} < (V+) - 2\text{ V}$ (Main input pair)			75	95	
		$V_S = 2.7 - 16\text{ V}, (V+) - 1\text{ V} < V_{CM} < (V+) + 0.1\text{ V}$ (Aux input pair)				80	
		$(V+) - 2\text{ V} < V_{CM} < (V+) - 1\text{ V}$			See Offset Voltage (Transition Region) in the <i>Typical Characteristics</i> section		
INPUT CAPACITANCE							
Z_{ID}	Differential				$100 \parallel 3$		$\text{M}\Omega \parallel \text{pF}$
Z_{ICM}	Common-mode				$6 \parallel 1$		$\text{T}\Omega \parallel \text{pF}$
OPEN-LOOP GAIN							
A_{OL}	Open-loop voltage gain	$V_S = 16\text{ V}, V_{CM} = V- (V-) + 0.1\text{ V} < V_O < (V+) - 0.1\text{ V}$	$T_A = -40^\circ\text{C to }125^\circ\text{C}$		115	135	dB
		$V_S = 4\text{ V}, V_{CM} = V- (V-) + 0.1\text{ V} < V_O < (V+) - 0.1\text{ V}$			104	125	dB
FREQUENCY RESPONSE							
GBW	Gain-bandwidth product				1.1		MHz
SR	Slew rate	$V_S = 16\text{ V}, G = +1, C_L = 20\text{ pF}$			4.5		$\text{V}/\mu\text{s}$
t_s	Settling time	To 0.1%, $V_S = 16\text{ V}, V_{STEP} = 10\text{ V}, G = +1, C_L = 20\text{ pF}$			4		μs
		To 0.1%, $V_S = 16\text{ V}, V_{STEP} = 2\text{ V}, G = +1, C_L = 20\text{ pF}$			2		
		To 0.01%, $V_S = 16\text{ V}, V_{STEP} = 10\text{ V}, G = +1, C_L = 20\text{ pF}$			5		
		To 0.01%, $V_S = 16\text{ V}, V_{STEP} = 2\text{ V}, G = +1, C_L = 20\text{ pF}$			3		
	Phase margin	$G = +1, R_L = 10\text{ k}\Omega, C_L = 20\text{ pF}$			60		$^\circ$
	Overload recovery time	$V_{IN} \times \text{gain} > V_S$			600		ns
THD+N	Total harmonic distortion + noise	$V_S = 16\text{ V}, V_O = 1\text{ V}_{RMS}, G = -1, f = 1\text{ kHz}$			0.0028%		
OUTPUT							
	Voltage output swing from rail	Positive and negative rail headroom	$V_S = 16\text{ V}, R_L = \text{no load}$		3		mV
			$V_S = 16\text{ V}, R_L = 10\text{ k}\Omega$		45	60	
			$V_S = 16\text{ V}, R_L = 2\text{ k}\Omega$		200	300	
			$V_S = 2.7\text{ V}, R_L = \text{no load}$		1		
			$V_S = 2.7\text{ V}, R_L = 10\text{ k}\Omega$		5	20	
			$V_S = 2.7\text{ V}, R_L = 2\text{ k}\Omega$		25	50	
I_{SC}	Short-circuit current				± 80		mA
C_{LOAD}	Capacitive load drive			See Small-Signal Overshoot vs Capacitive Load in the <i>Typical Characteristics</i> section			
Z_O	Open-loop output impedance	$f = 1\text{ MHz}, I_O = 0\text{ A}$			600		Ω

For $V_S = (V+) - (V-) = 2.7\text{ V to }16\text{ V}$ ($\pm 1.35\text{ V to } \pm 8\text{ V}$) at $T_A = 25^\circ\text{C}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{O\ UT} = V_S / 2$, unless otherwise noted.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
POWER SUPPLY							
I_Q	Quiescent current per amplifier	$I_O = 0\text{A}$			115	150	μA
			$T_A = -40^\circ\text{C to }125^\circ\text{C}$			160	

5.6 Typical Characteristics

at $T_A = 25^\circ\text{C}$, $V_S = \pm 8\text{V}$, $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 100\text{pF}$ (unless otherwise noted)

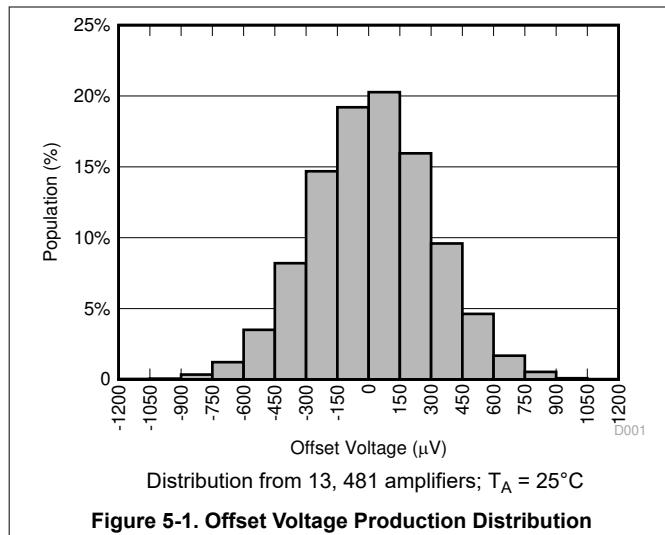


Figure 5-1. Offset Voltage Production Distribution

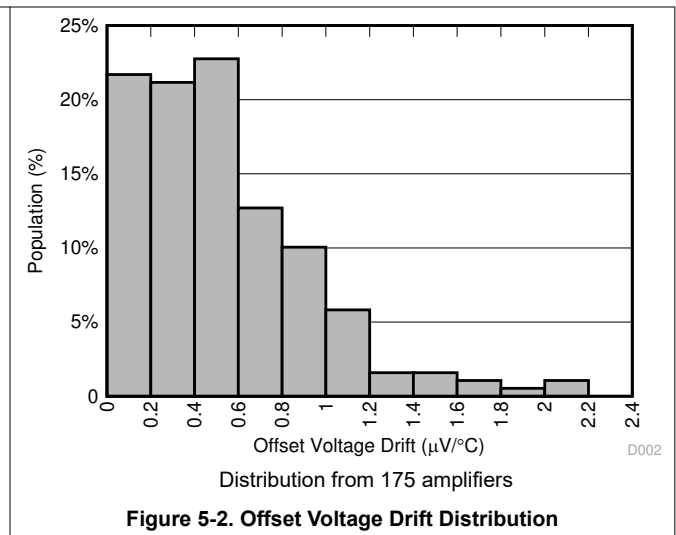


Figure 5-2. Offset Voltage Drift Distribution

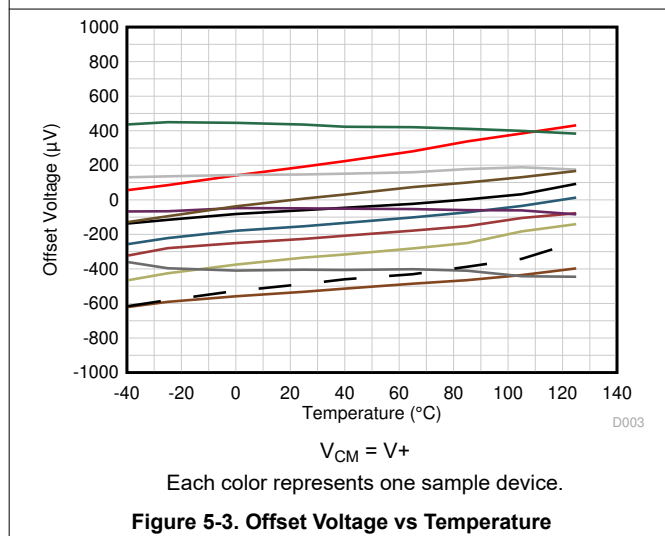


Figure 5-3. Offset Voltage vs Temperature

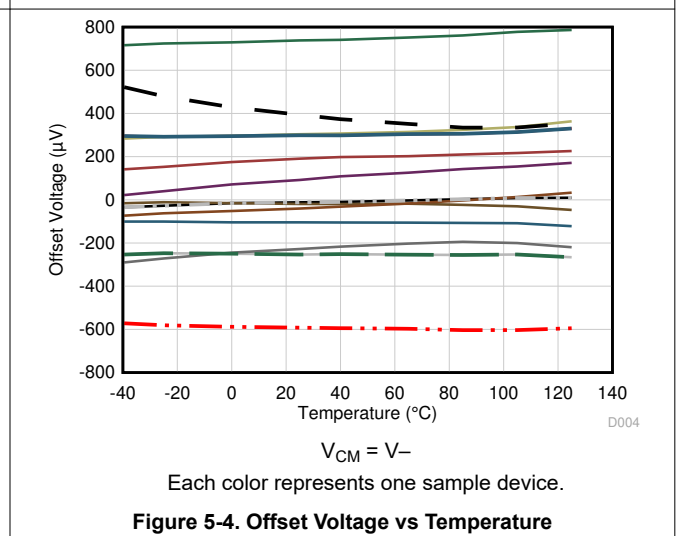


Figure 5-4. Offset Voltage vs Temperature

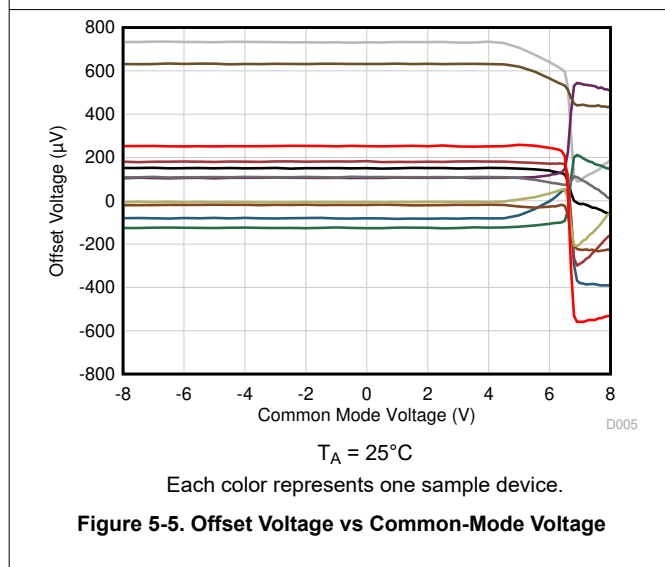


Figure 5-5. Offset Voltage vs Common-Mode Voltage

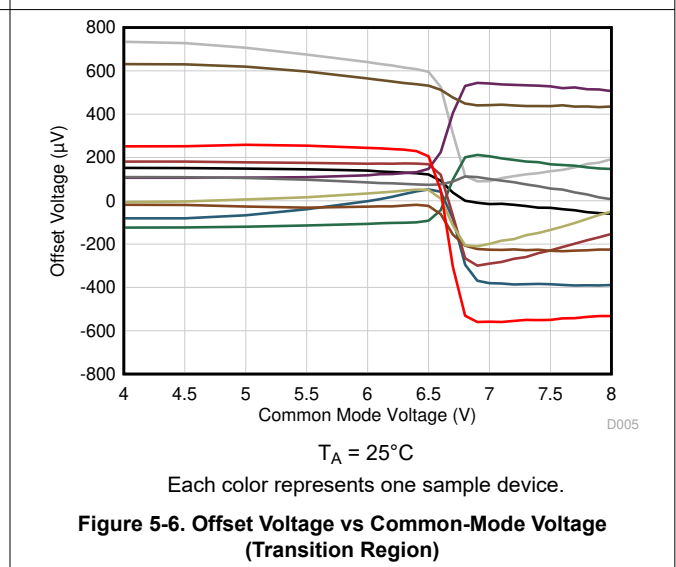


Figure 5-6. Offset Voltage vs Common-Mode Voltage (Transition Region)

5.6 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 8\text{V}$, $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 100\text{pF}$ (unless otherwise noted)

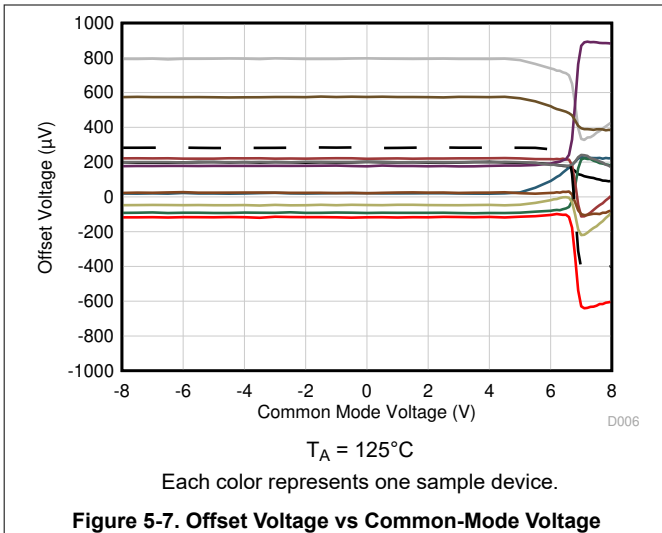


Figure 5-7. Offset Voltage vs Common-Mode Voltage

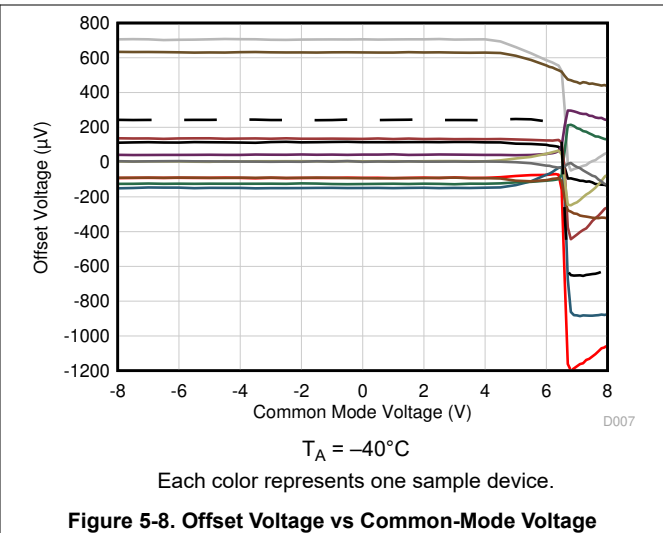


Figure 5-8. Offset Voltage vs Common-Mode Voltage

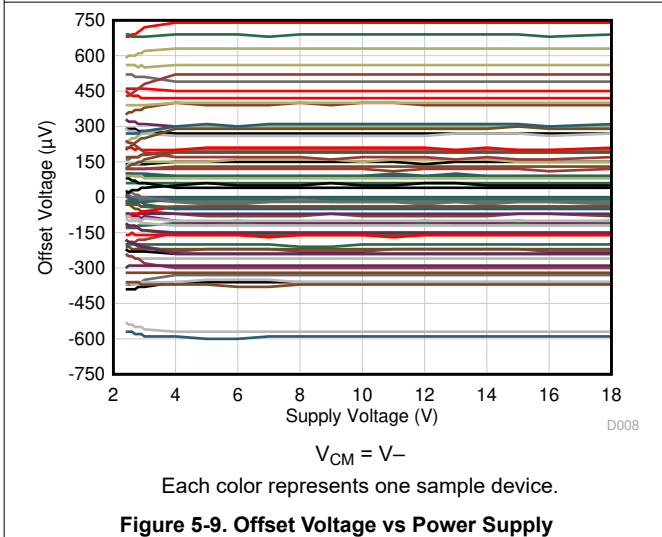


Figure 5-9. Offset Voltage vs Power Supply

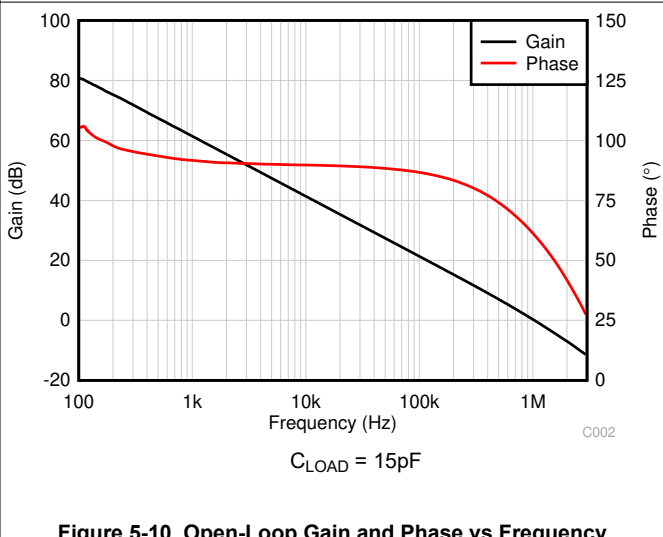


Figure 5-10. Open-Loop Gain and Phase vs Frequency

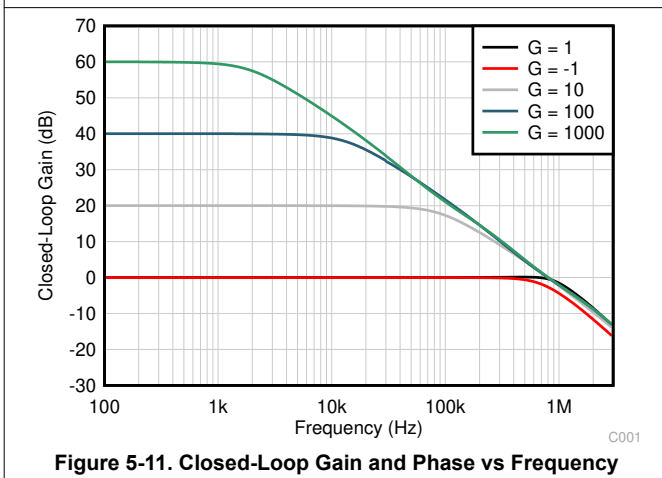


Figure 5-11. Closed-Loop Gain and Phase vs Frequency

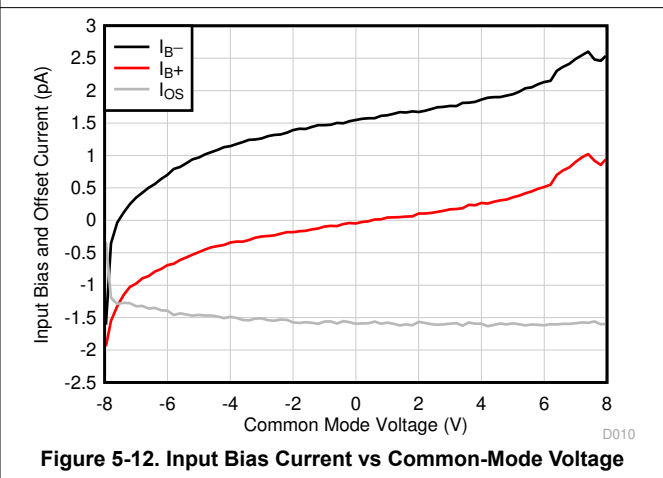


Figure 5-12. Input Bias Current vs Common-Mode Voltage

5.6 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 8\text{V}$, $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 100\text{pF}$ (unless otherwise noted)

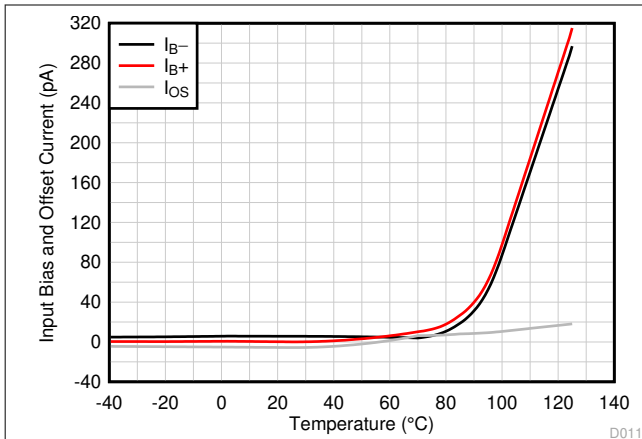


Figure 5-13. Input Bias Current vs Temperature

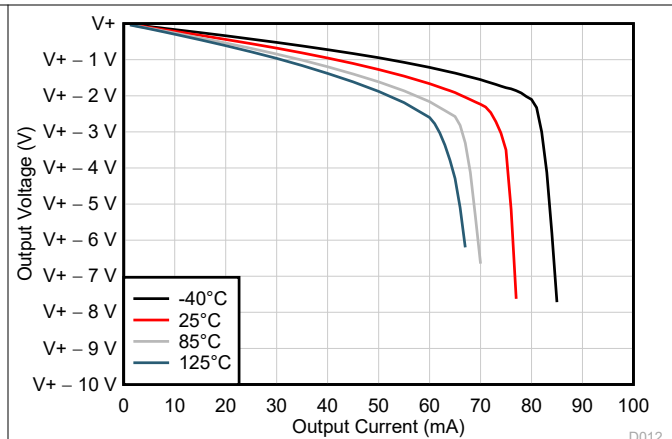


Figure 5-14. Output Voltage Swing vs Output Current (Sourcing)

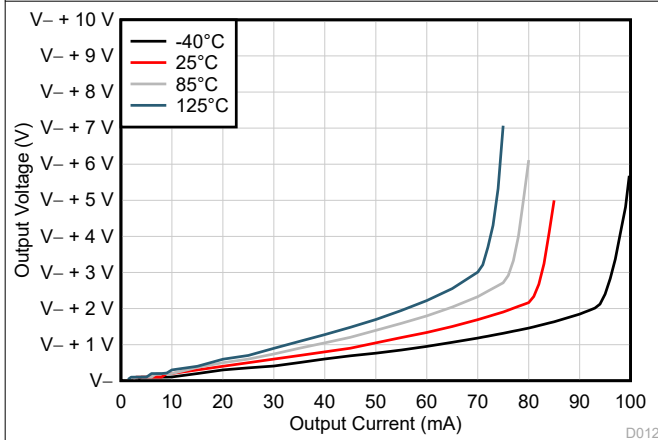


Figure 5-15. Output Voltage Swing vs Output Current (Sinking)

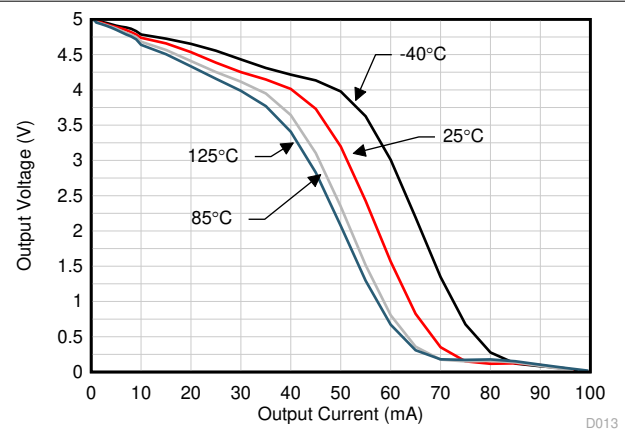


Figure 5-16. Output Voltage Swing vs Output Current (Sourcing)

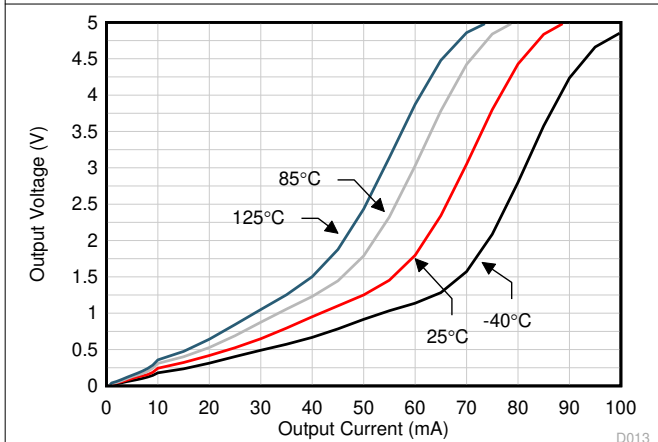


Figure 5-17. Output Voltage Swing vs Output Current (Sinking)

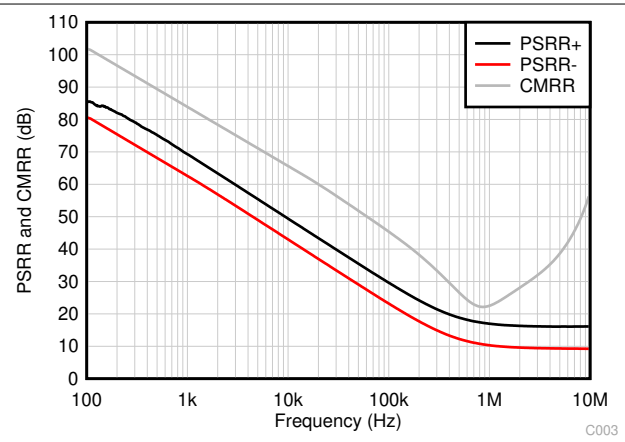


Figure 5-18. CMRR and PSRR vs Frequency

5.6 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 8\text{V}$, $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 100\text{pF}$ (unless otherwise noted)

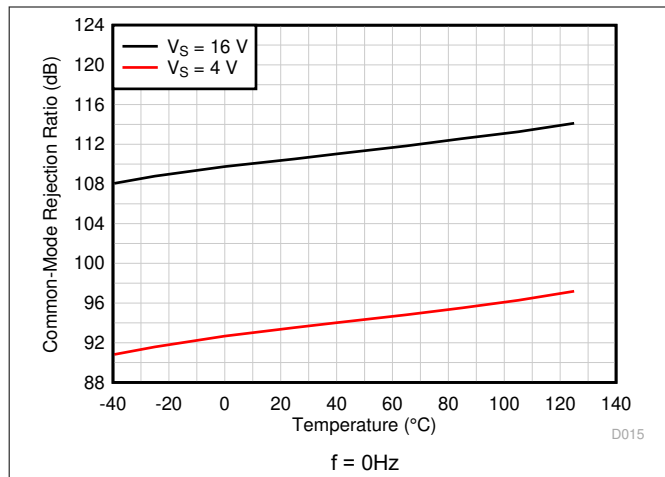


Figure 5-19. CMRR vs Temperature (dB)

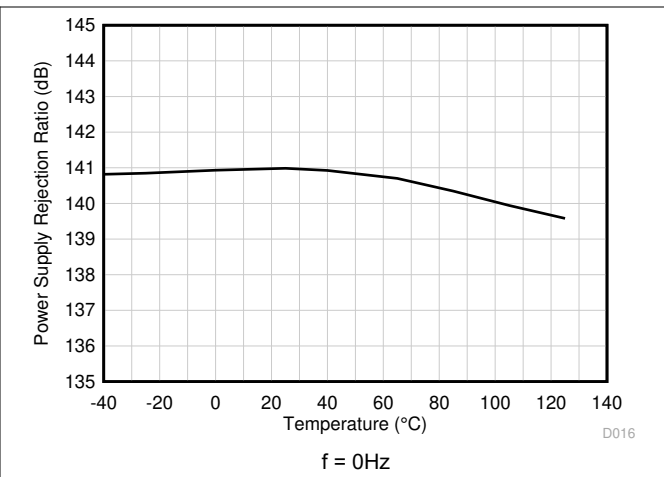


Figure 5-20. PSRR vs Temperature (dB)

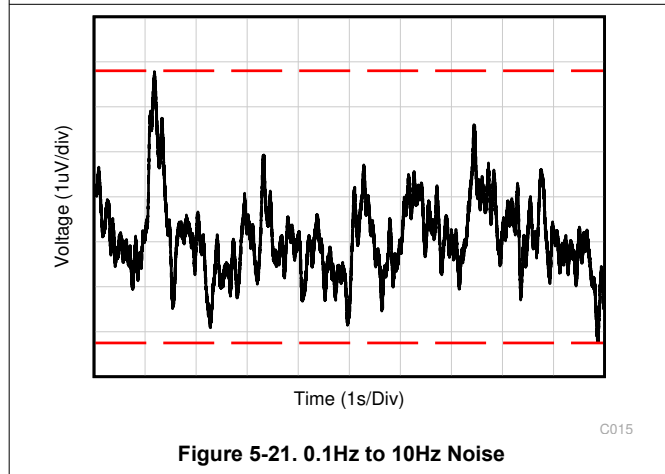


Figure 5-21. 0.1Hz to 10Hz Noise

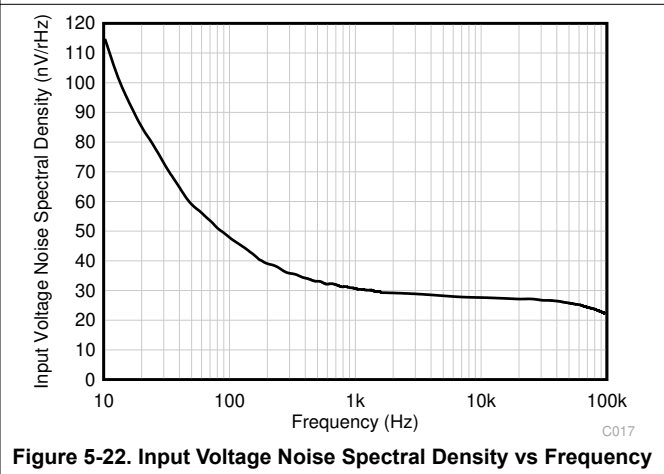


Figure 5-22. Input Voltage Noise Spectral Density vs Frequency

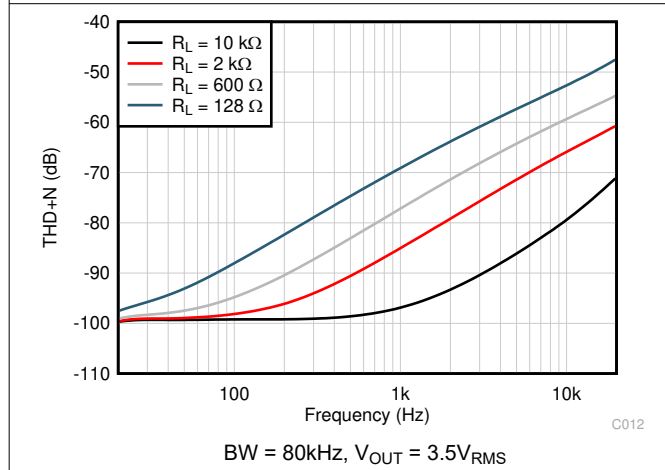


Figure 5-23. THD+N Ratio vs Frequency

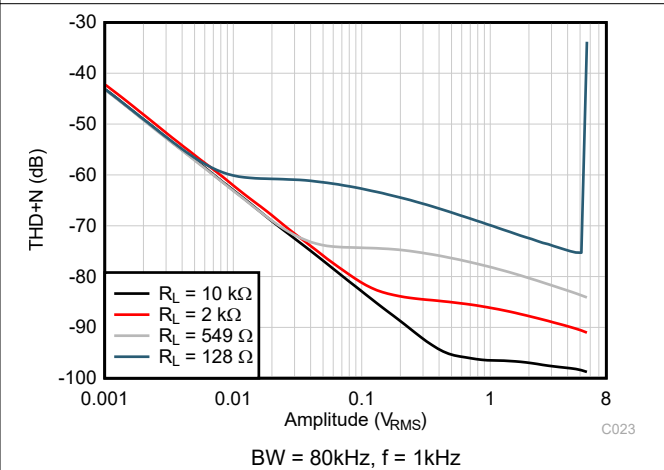


Figure 5-24. THD+N vs Output Amplitude

5.6 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 8\text{V}$, $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 100\text{pF}$ (unless otherwise noted)

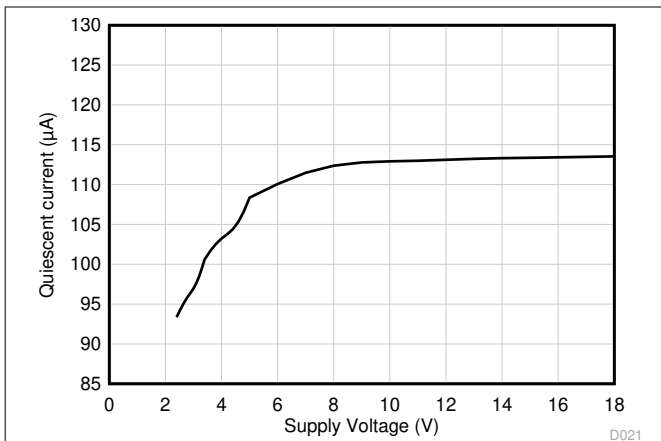


Figure 5-25. Quiescent Current per Channel vs Supply Voltage

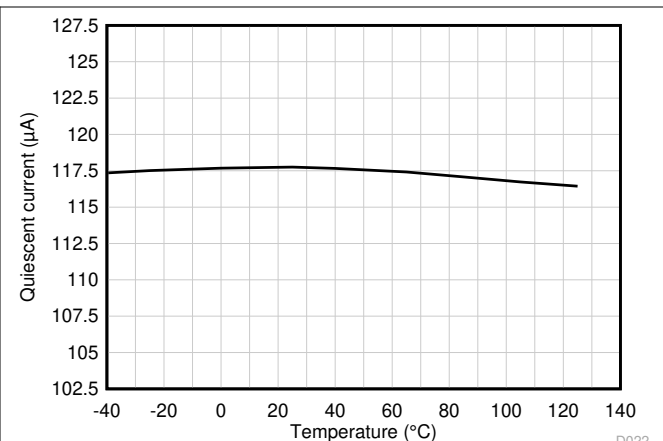


Figure 5-26. Quiescent Current per Channel vs Temperature

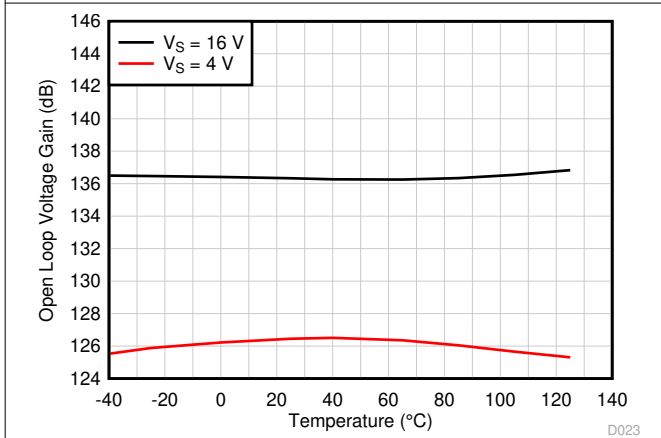


Figure 5-27. Open-Loop Voltage Gain vs Temperature (dB)

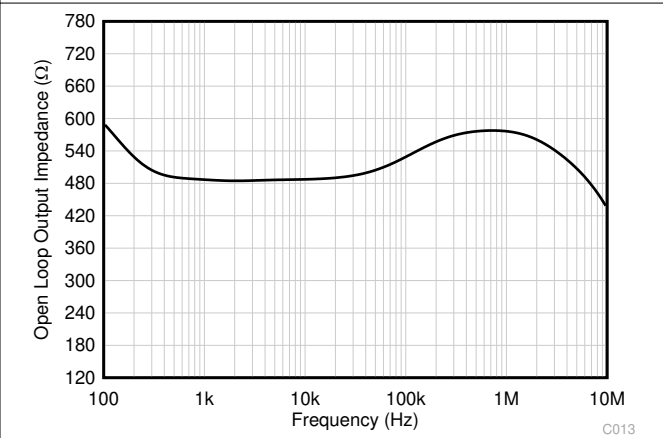
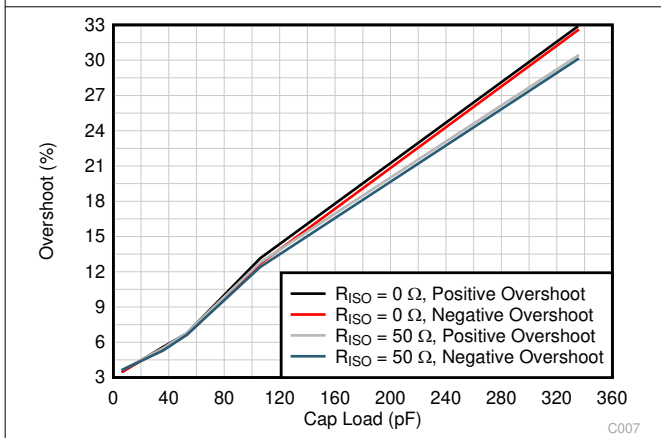
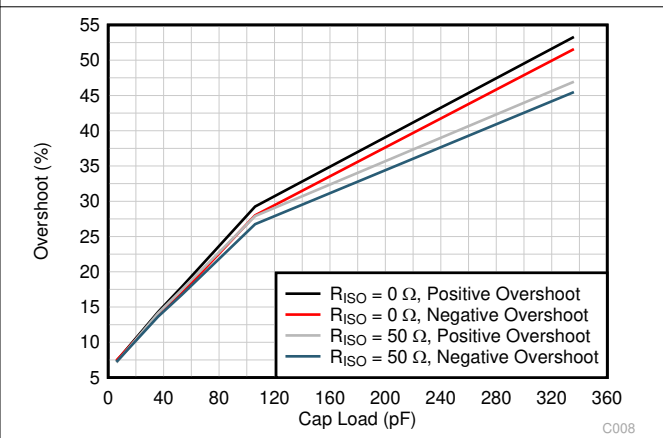


Figure 5-28. Open-Loop Output Impedance vs Frequency



$G = -1$, 100mV output step

Figure 5-29. Small-Signal Overshoot vs Capacitive Load



$G = 1$, 100mV output step

Figure 5-30. Small-Signal Overshoot vs Capacitive Load

5.6 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 8\text{V}$, $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 100\text{pF}$ (unless otherwise noted)

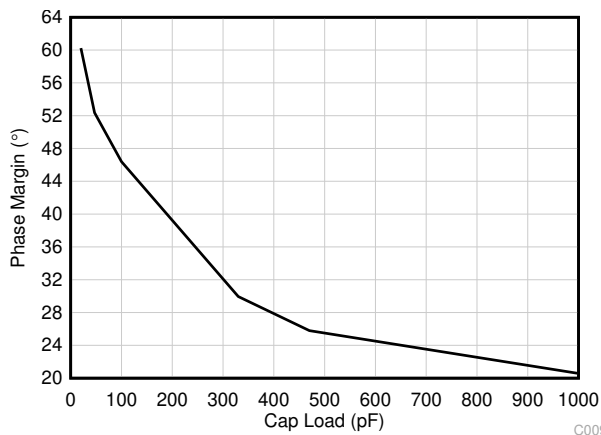


Figure 5-31. Small-Signal Overshoot vs Capacitive Load

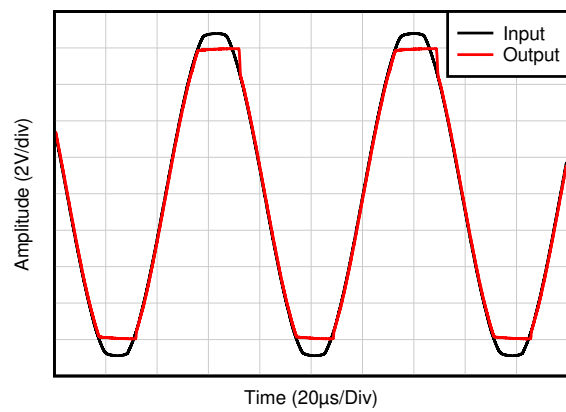


Figure 5-32. No Phase Reversal

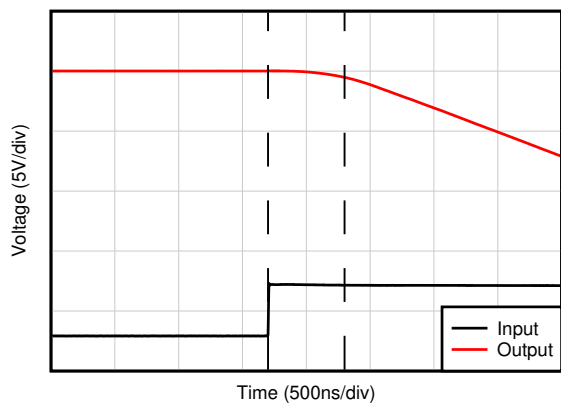


Figure 5-33. Positive Overload Recovery

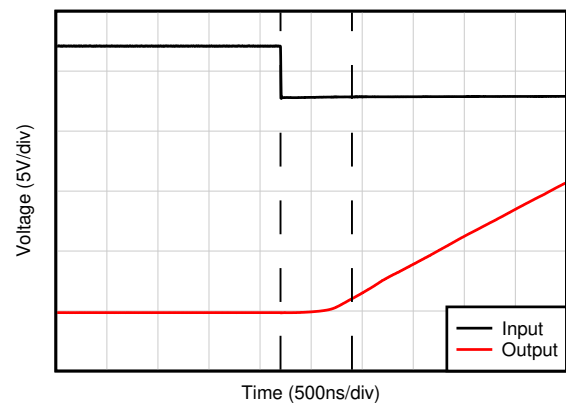


Figure 5-34. Negative Overload Recovery

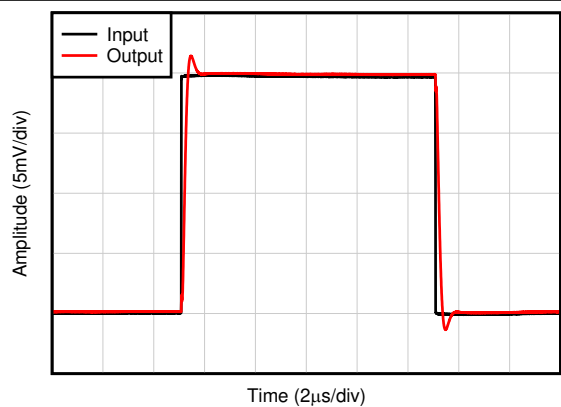


Figure 5-35. Small-Signal Step Response

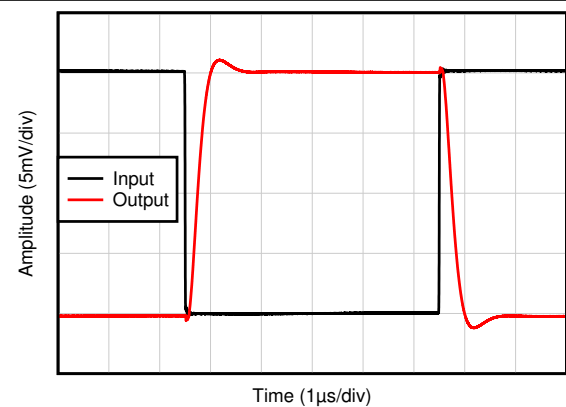
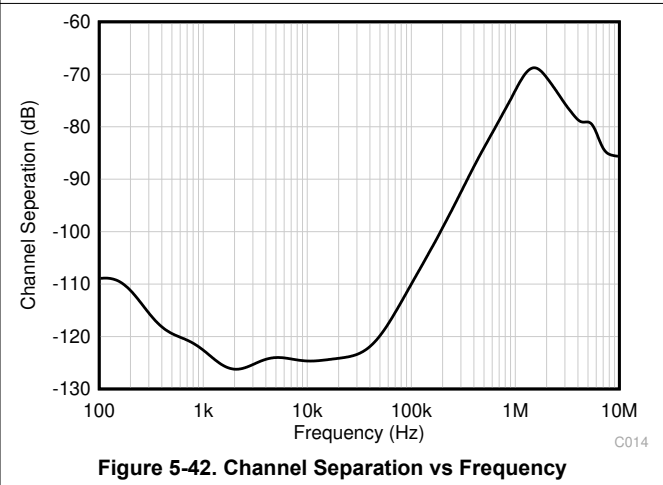
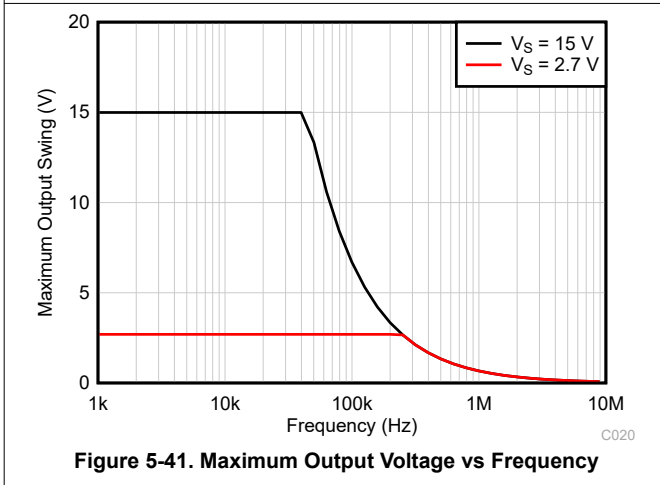
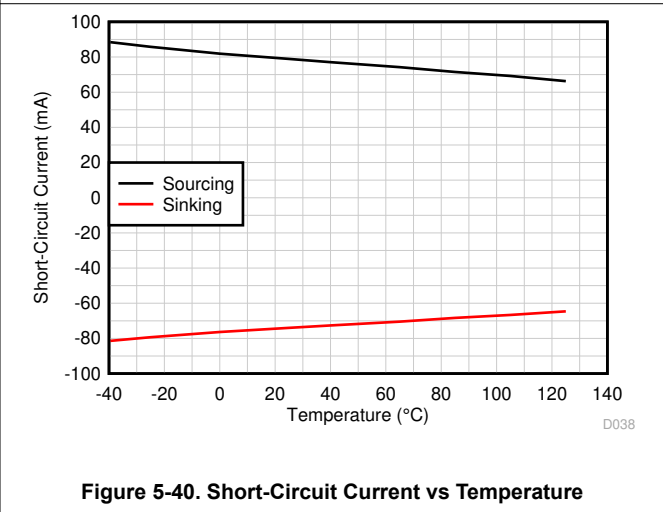
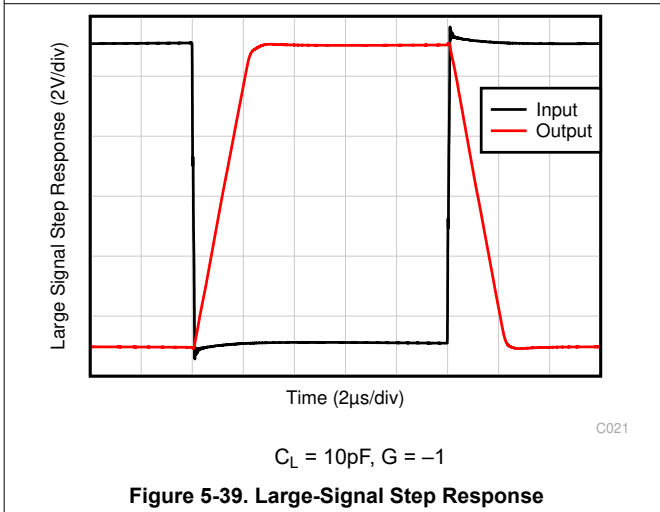
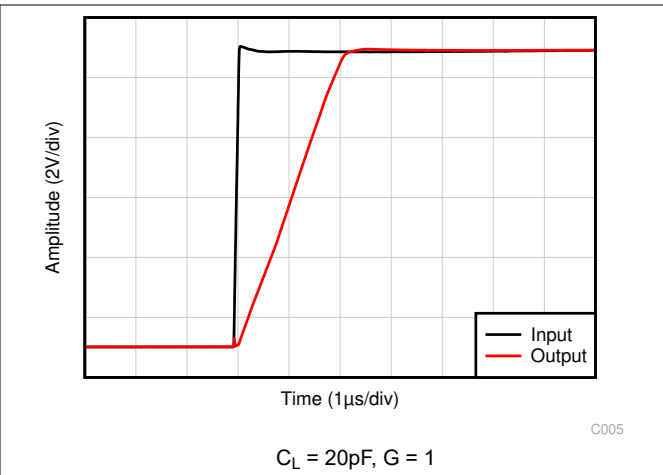
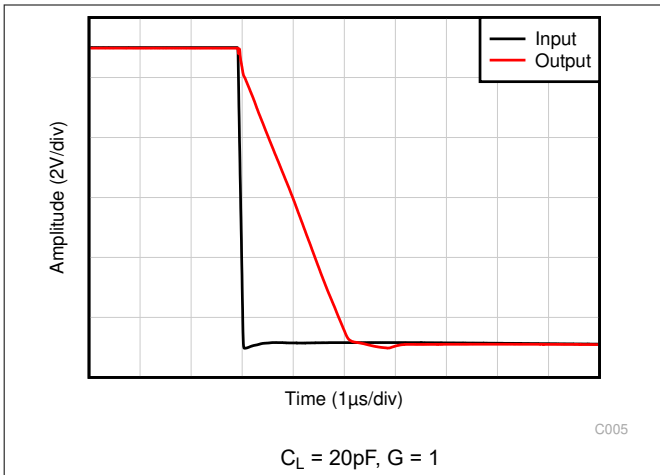


Figure 5-36. Small-Signal Step Response

5.6 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 8\text{V}$, $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 100\text{pF}$ (unless otherwise noted)



5.6 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = \pm 8\text{V}$, $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 100\text{pF}$ (unless otherwise noted)

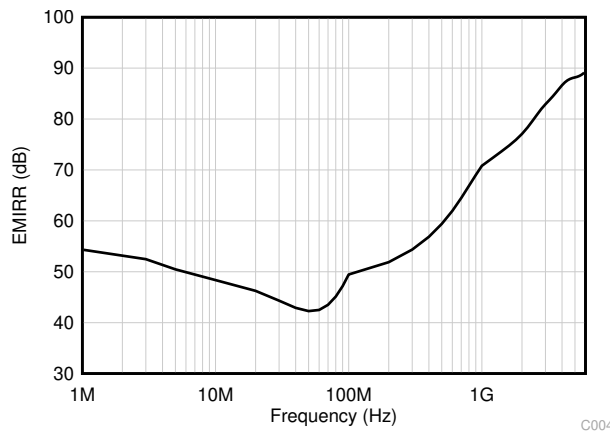


Figure 5-43. EMIRR (Electromagnetic Interference Rejection Ratio) vs Frequency

6 Detailed Description

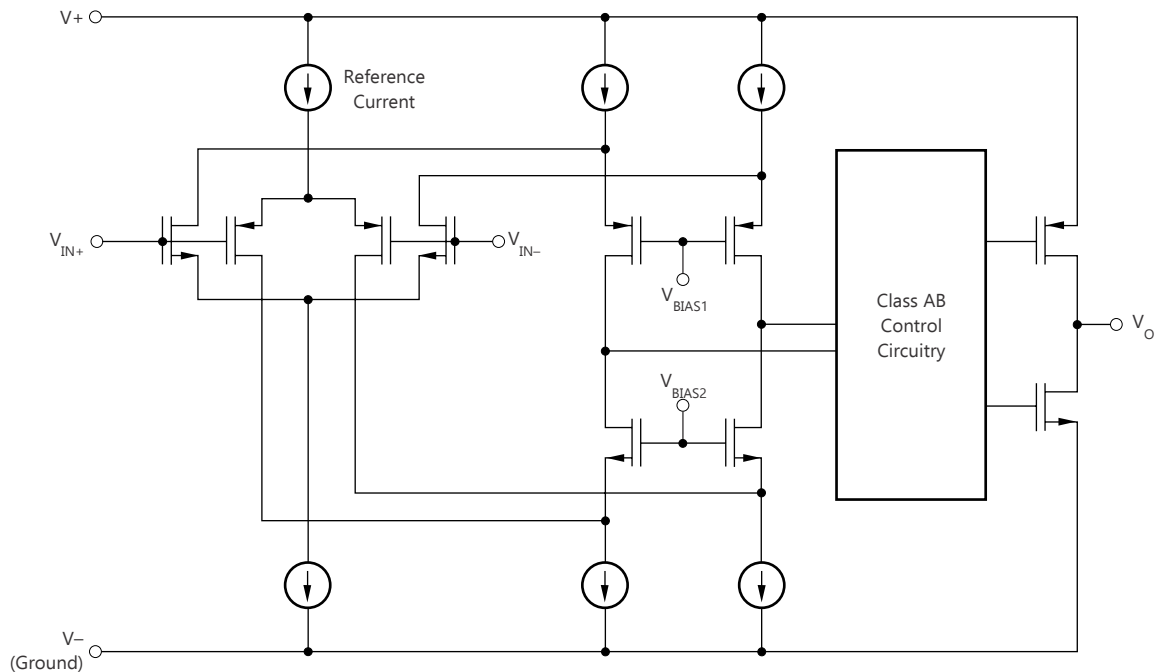
6.1 Overview

The TLV910x-Q1 family (TLV9101-Q1, TLV9102-Q1, and TLV9104-Q1) is a family of 16V general purpose operational amplifiers.

These devices offer excellent DC precision and AC performance, including rail-to-rail input/output, low offset ($\pm 300\mu\text{V}$, typical), low offset drift ($\pm 0.6\mu\text{V}/^\circ\text{C}$, typical), and 1.1MHz bandwidth.

Wide differential and common-mode input-voltage range, high output current ($\pm 80\text{mA}$), high slew rate ($4.5\text{V}/\mu\text{s}$), low power operation ($120\mu\text{A}$, typical), and shutdown functionality make the TLV910x-Q1 a robust, low-power, high-performance operational amplifier for industrial applications.

6.2 Functional Block Diagram



6.3 Feature Description

6.3.1 EMI Rejection

The TLV910x-Q1 uses integrated electromagnetic interference (EMI) filtering to reduce the effects of EMI from sources such as wireless communications and densely-populated boards with a mix of analog signal chain and digital components. EMI immunity can be improved with circuit design techniques, and the TLV910x-Q1 benefits from these design improvements. Texas Instruments has developed the ability to accurately measure and quantify the immunity of an operational amplifier over a broad frequency spectrum extending from 10MHz to 6GHz. Figure 6-1 shows the results of this testing on the TLV910x-Q1. Table 6-1 shows the EMIRR IN+ values for the TLV910x-Q1 at particular frequencies commonly encountered in real-world applications. Table 6-1 lists applications that can be centered on or operated near the particular frequency shown. The *EMI Rejection Ratio of Operational Amplifiers* application report contains detailed information on the topic of EMIRR performance of op amps and is available for download from www.ti.com.

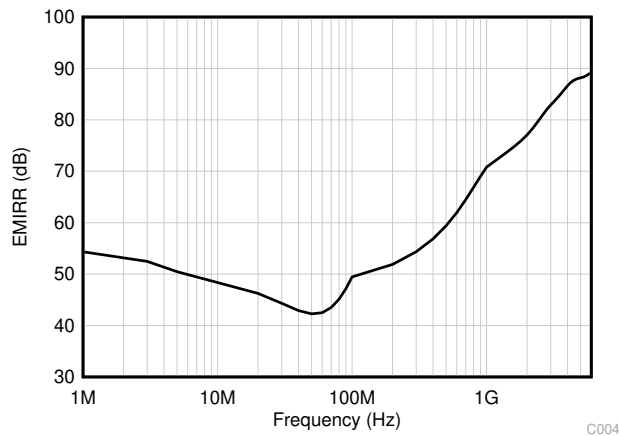


Figure 6-1. TLV910x-Q1 EMIRR Testing

Table 6-1. TLV910x-Q1 EMIRR IN+ for Frequencies of Interest

FREQUENCY	APPLICATION OR ALLOCATION	EMIRR IN+
400MHz	Mobile radio, mobile satellite, space operation, weather, radar, ultra-high frequency (UHF) applications	59.5dB
900MHz	Global system for mobile communications (GSM) applications, radio communication, navigation, GPS (to 1.6GHz), GSM, aeronautical mobile, UHF applications	68.9dB
1.8GHz	GSM applications, mobile personal communications, broadband, satellite, L-band (1GHz to 2GHz)	77.8dB
2.4GHz	802.11b, 802.11g, 802.11n, Bluetooth®, mobile personal communications, industrial, scientific and medical (ISM) radio band, amateur radio and satellite, S-band (2GHz to 4GHz)	78.0dB
3.6GHz	Radiolocation, aero communication and navigation, satellite, mobile, S-band	88.8dB
5GHz	802.11a, 802.11n, aero communication and navigation, mobile communication, space and satellite operation, C-band (4GHz to 8GHz)	87.6dB

6.3.2 Phase Reversal Protection

The TLV910x-Q1 family has internal phase-reversal protection. Many op amps exhibit a phase reversal when the input is driven beyond the linear common-mode range. This condition is most often encountered in noninverting circuits when the input is driven beyond the specified common-mode voltage range, causing the output to reverse into the opposite rail. The TLV910x-Q1 is a rail-to-rail input op amp, therefore the common-mode range can extend up to the rails. Input signals beyond the rails do not cause phase reversal. Instead, the output limits into the appropriate rail. Figure 6-2 shows this performance.

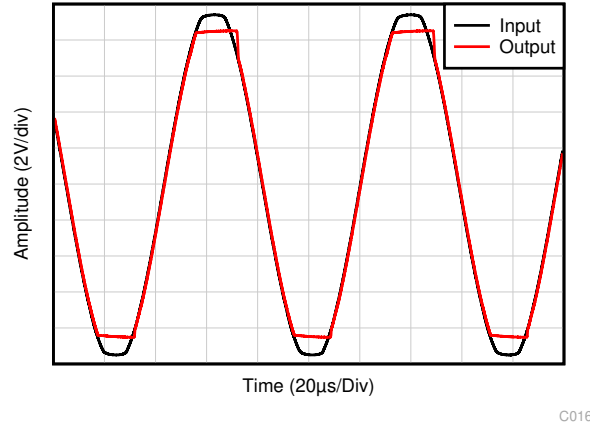


Figure 6-2. No Phase Reversal

6.3.3 Thermal Protection

The internal power dissipation of any amplifier causes the internal (junction) temperature to rise. This phenomenon is called *self heating*. The absolute maximum junction temperature of the TLV910x-Q1 is 150°C. Exceeding this temperature causes damage to the device. The TLV910x-Q1 has a thermal protection feature that prevents damage from self heating. The protection works by monitoring the temperature of the device and turning off the op amp output drive for temperatures above 140°C. Figure 6-3 shows an application example for the TLV9101-Q1 that has significant self heating (154°C) because of the power dissipation (0.39W). Thermal calculations indicate that for an ambient temperature of 100°C, the device junction temperature must reach 154°C. The actual device, however, turns off the output drive to maintain a safe junction temperature. Figure 6-3 shows how the circuit behaves during thermal protection. During normal operation, the device acts as a buffer so the output is 3V. When self heating causes the device junction temperature to increase above 140°C, the thermal protection forces the output to a high-impedance state and the output is pulled to ground through resistor R_L .

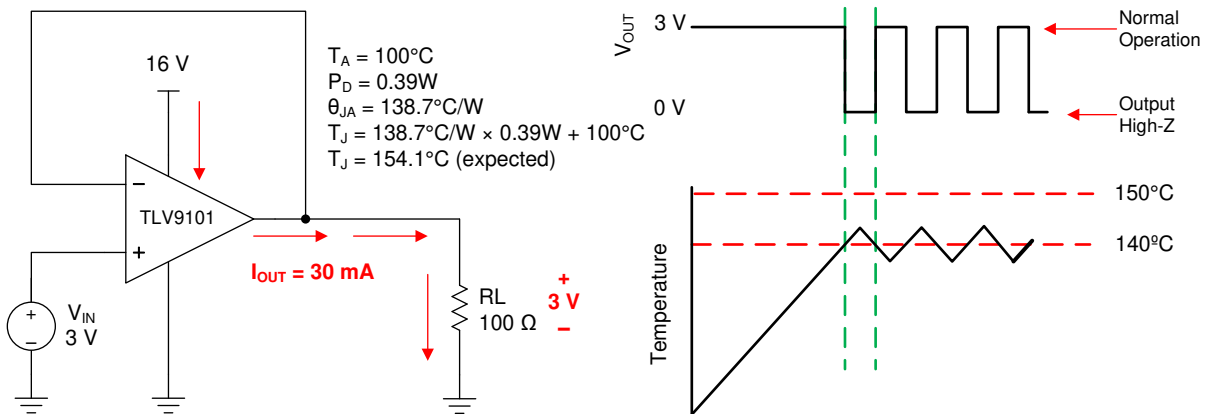
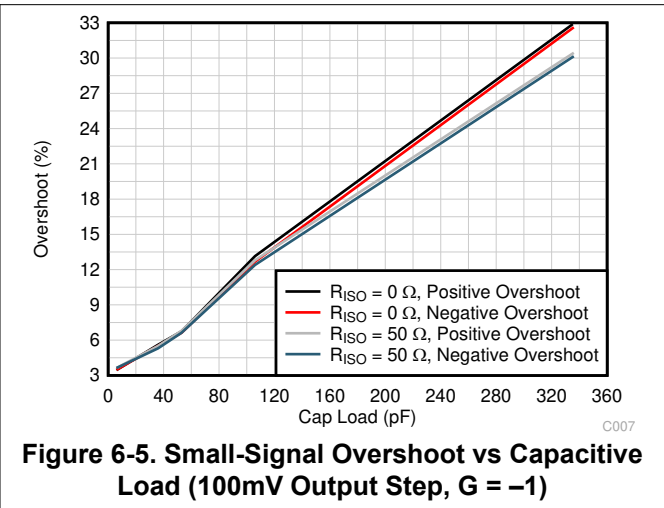
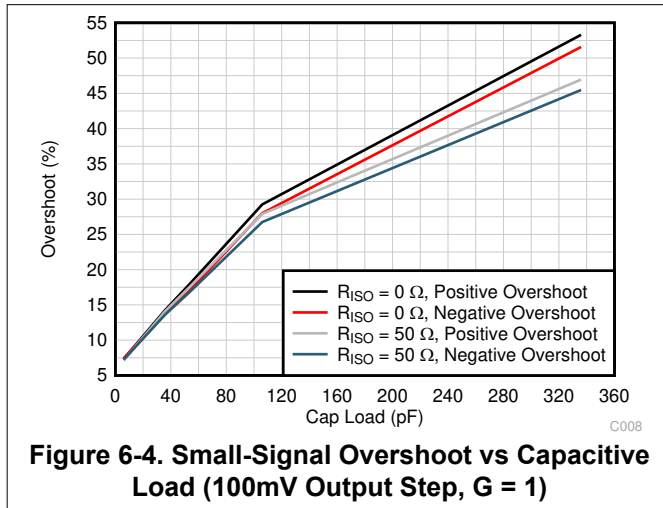


Figure 6-3. Thermal Protection

6.3.4 Capacitive Load and Stability

The TLV910x-Q1 features a resistive output stage capable of driving moderate capacitive loads, and by leveraging an isolation resistor, the device can easily be configured to drive large capacitive loads. Increasing the gain enhances the ability of the amplifier to drive greater capacitive loads (see Figure 6-4 and Figure 6-5). The particular op amp circuit configuration, layout, gain, and output loading are some of the factors to consider when establishing whether an amplifier is stable in operation.



For additional drive capability in unity-gain configurations, improve capacitive load drive by inserting a small (10 Ω to 20 Ω) resistor, R_{ISO} , in series with the output, as shown in Figure 6-6. This resistor significantly reduces ringing and maintains DC performance for purely capacitive loads. However, if a resistive load is in parallel with the capacitive load, then a voltage divider is created, thus introducing a gain error at the output and slightly reducing the output swing. The error introduced is proportional to the ratio R_{ISO} / R_L , and is generally negligible at low output levels. The high capacitive load drive of the TLV910x-Q1 is designed for applications like reference buffers, MOSFET gate drives, and cable-shield drives. The circuit shown in Figure 6-6 uses an isolation resistor, R_{ISO} , to stabilize the output of an op amp. R_{ISO} modifies the open-loop gain of the system for increased phase margin.

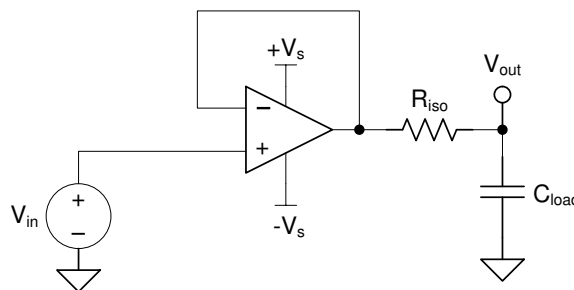


Figure 6-6. Extending Capacitive Load Drive With the TLV9101-Q1

6.3.5 Common-Mode Voltage Range

The TLV910x-Q1 is a 16V, true rail-to-rail input operational amplifier with an input common-mode range that extends 100mV beyond either supply rail. This wide range is achieved with paralleled complementary N-channel and P-channel differential input pairs, as shown in Figure 6-7. The N-channel pair is active for input voltages close to the positive rail, typically $(V+) - 1V$ to 100mV above the positive supply. The P-channel pair is active for inputs from 100mV below the negative supply to approximately $(V+) - 2V$. There is a small transition region, typically $(V+) - 2V$ to $(V+) - 1V$ in which both input pairs are on. This transition region can vary modestly with process variation, and within this region PSRR, CMRR, offset voltage, offset drift, noise, and THD performance can be degraded compared to operation outside this region. To achieve best performance with the TLV910x-Q1 family, avoid this transition region when possible.

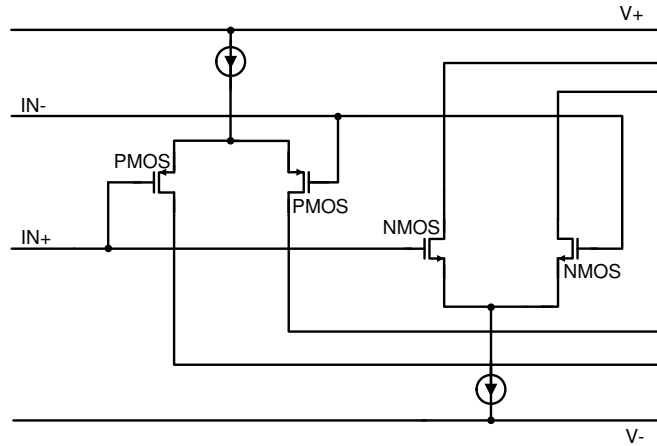


Figure 6-7. Rail-to-Rail Input Stage

6.3.6 Electrical Overstress

Designers often ask questions about the capability of an operational amplifier to withstand electrical overstress (EOS). These questions tend to focus on the device inputs, but can involve the supply voltage pins or even the output pin. Each of these different pin functions have electrical stress limits determined by the voltage breakdown characteristics of the particular semiconductor fabrication process and specific circuits connected to the pin. Additionally, internal electrostatic discharge (ESD) protection is built into these circuits to protect them from accidental ESD events both before and during product assembly.

Having a good understanding of this basic ESD circuitry and the relevance to an electrical overstress event is helpful. Figure 6-8 shows an illustration of the ESD circuits contained in the TLV910x-Q1 (indicated by the dashed line area). The ESD protection circuitry involves several current-steering diodes connected from the input and output pins and routed back to the internal power-supply lines, where the diodes meet at an absorption device or the power-supply ESD cell, internal to the operational amplifier. This protection circuitry is intended to remain inactive during normal circuit operation.

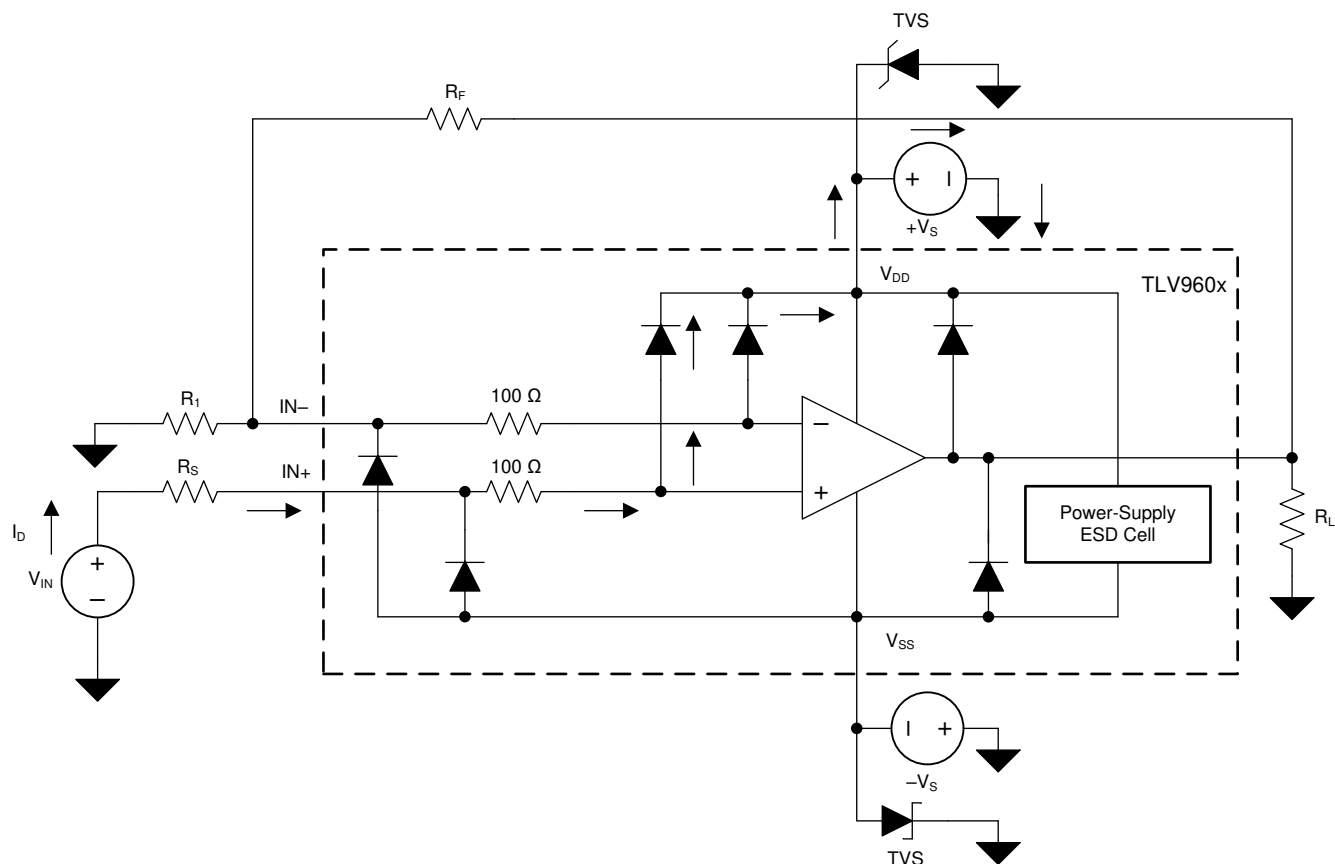


Figure 6-8. Equivalent Internal ESD Circuitry Relative to a Typical Circuit Application

An ESD event is very short in duration and very high voltage (for example, 1kV, 100ns), whereas an EOS event is long duration and lower voltage (for example, 50V, 100ms). The ESD diodes are designed for out-of-circuit ESD protection (that is, during assembly, test, and storage of the device before being soldered to the PCB). During an ESD event, the ESD signal is passed through the ESD steering diodes to an absorption circuit (labeled ESD power-supply circuit). The ESD absorption circuit clamps the supplies to a safe level.

Although this behavior is necessary for out-of-circuit protection, excessive current and damage is caused if activated in-circuit. A transient voltage suppressors (TVS) can be used to prevent damage caused by turning on the ESD absorption circuit during an in-circuit ESD event. Using the appropriate current limiting resistors and TVS diodes allows for the use of device ESD diodes to protect against EOS events.

6.3.7 Overload Recovery

Overload recovery is defined as the time required for the op amp output to recover from a saturated state to a linear state. The output devices of the op amp enter a saturation region when the output voltage exceeds the rated operating voltage, either due to the high input voltage or the high gain. After the device enters the saturation region, the charge carriers in the output devices require time to return back to the linear state. After the charge carriers return back to the linear state, the device begins to slew at the specified slew rate. Thus, the propagation delay in case of an overload condition is the sum of the overload recovery time and the slew time. The overload recovery time for the TLV910x-Q1 is approximately 1μs.

6.3.8 Typical Specifications and Distributions

Designers often have questions about a typical specification of an amplifier to design a more robust circuit. Due to natural variation in process technology and manufacturing procedures, every specification of an amplifier exhibits some amount of deviation from the expected value, like the input offset voltage of an amplifier. These deviations often follow *Gaussian* ("bell curve"), or *normal* distributions, and circuit designers can leverage this information to guardband a system, even when there is not a minimum or maximum specification in [Electrical Characteristics](#).

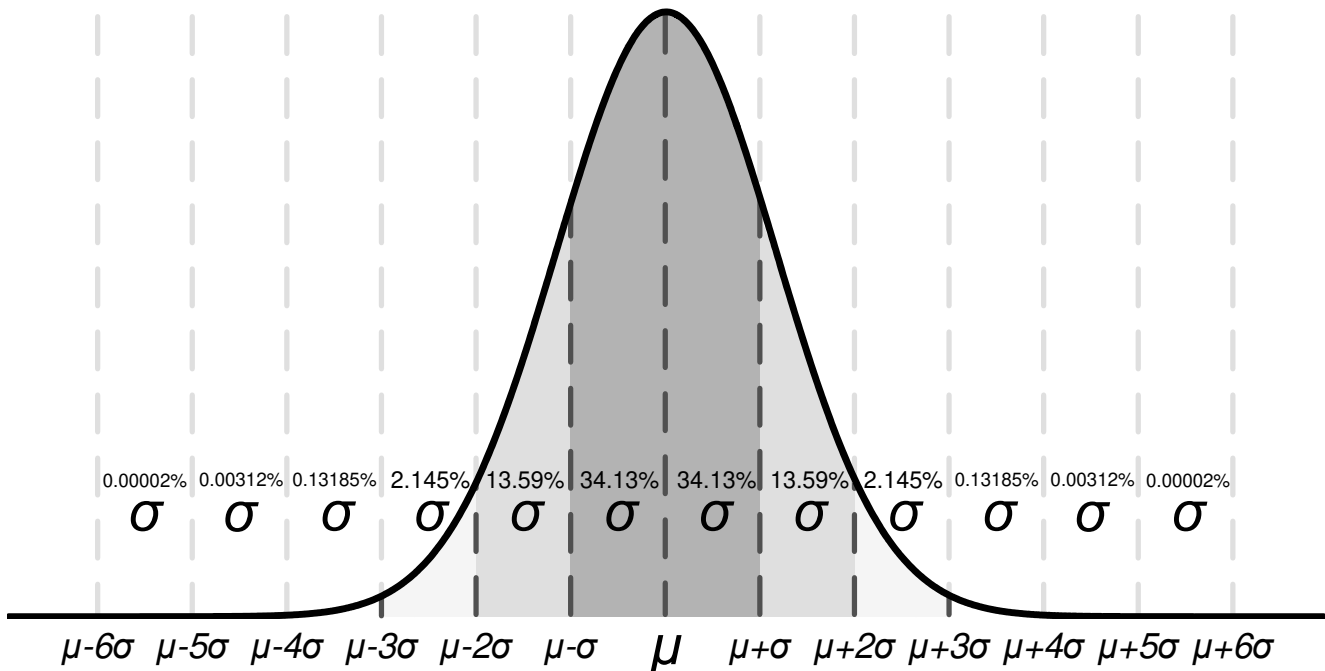


Figure 6-9. Gaussian Distribution

Figure 6-9 shows an example distribution, where μ , or *mu*, is the mean of the distribution, and where σ , or *sigma*, is the standard deviation of a system. For a specification that exhibits this kind of distribution,

approximately two-thirds (68.26%) of all units can be expected to have a value within one standard deviation, or one sigma, of the mean (from $\mu - \sigma$ to $\mu + \sigma$).

Depending on the specification, values listed in the *typical* column of [Electrical Characteristics](#) are represented in different ways. As a general rule, if a specification naturally has a nonzero mean (for example, gain bandwidth), then the typical value is equal to the mean (μ). However, if a specification naturally has a mean near zero (like input offset voltage), then the typical value is equal to the mean plus one standard deviation ($\mu + \sigma$) to most accurately represent the typical value.

You can use this chart to calculate approximate probability of a specification in a unit; for example, for TLV910x-Q1, the typical input voltage offset is 300 μ V, so 68.2% of all TLV910x-Q1 devices are expected to have an offset from -300μ V to $+300\mu$ V. At 4σ ($\pm 1200\mu$ V), 99.9937% of the distribution has an offset voltage less than $\pm 1200\mu$ V, which means 0.0063% of the population is outside of these limits, which corresponds to about 1 in 15,873 units.

Specifications with a value in the minimum or maximum column are specified by TI, and units outside these limits are removed from production material. For example, the TLV910x-Q1 family has a maximum offset voltage of 1.5mV at 25°C, and even though this corresponds to 5σ (≈ 1 in 1.7 million units), which is extremely unlikely, TI removes any unit with larger offset than 1.5mV from production material.

For specifications with no value in the minimum or maximum column, consider selecting a sigma value of sufficient guardband for your application, and design worst-case conditions using this value. For example, the 6σ value corresponds to about 1 in 500 million units, which is an extremely unlikely chance and can be an option as a wide guardband to design a system around. In this case, the TLV910x-Q1 family does not have a maximum or minimum for offset voltage drift, but based on [Figure 5-2](#) and the typical value of 0.6 μ V/°C in [Electrical Characteristics](#), the 6σ value for offset voltage drift is about 3.6 μ V/°C. When designing for worst-case system conditions, this value can be used to estimate the worst possible offset across temperature without having an actual minimum or maximum value.

However, process variation and adjustments over time can shift typical means and standard deviations, and unless there is a value in the minimum or maximum specification column, TI cannot specify the performance of a device. This information is intended to be used only to estimate the performance of a device.

6.4 Device Functional Modes

The TLV910x-Q1 has a single functional mode and is operational when the power-supply voltage is greater than 2.7V (± 1.35 V). The maximum power supply voltage for the TLV910x-Q1 is 16V (± 8 V).

7 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

7.1 Application Information

The TLV910x-Q1 family offers excellent DC precision and DC performance. These devices operate up to 16V supply rails and offer true rail-to-rail input/output, low offset voltage and offset voltage drift, as well as 1.1MHz bandwidth and high output drive. These features make the TLV910x-Q1 a robust, high-performance operational amplifier for high-voltage automotive applications.

7.2 Typical Applications

7.2.1 Low-Side Current Measurement

Figure 7-1 shows the TLV910x-Q1 configured in a low-side current sensing application. For a full analysis of the circuit shown in Figure 7-1 including theory, calculations, simulations, and measured data, see TI Precision Design TIPD129, *0A to 1A Single-Supply Low-Side Current-Sensing Solution*.

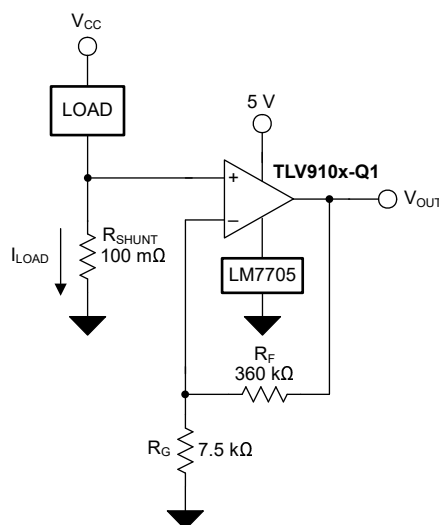


Figure 7-1. TLV910x-Q1 in a Low-Side, Current-Sensing Application

7.2.1.1 Design Requirements

The design requirements for this design are:

- Load current: 0A to 1A
- Output voltage: 4.9V
- Maximum shunt voltage: 100mV

7.2.1.2 Detailed Design Procedure

Use [Equation 1](#) to calculate the transfer function of the circuit in [Figure 7-1](#).

$$V_{OUT} = I_{LOAD} \times R_{SHUNT} \times \text{Gain} \quad (1)$$

The load current (I_{LOAD}) produces a voltage drop across the shunt resistor (R_{SHUNT}). The load current is set from 0A to 1A. To keep the shunt voltage below 100mV at maximum load current, use [Equation 2](#) to calculate the largest shunt resistor allowed.

$$R_{SHUNT} = \frac{V_{SHUNT_MAX}}{I_{LOAD_MAX}} = \frac{100 \text{ mV}}{1 \text{ A}} = 100 \text{ m}\Omega \quad (2)$$

Using [Equation 2](#), R_{SHUNT} is calculated to be 100m Ω . The voltage drop produced by I_{LOAD} and R_{SHUNT} is amplified by the TLV910x-Q1 to produce an output voltage of 0V to 4.9V. Use [Equation 3](#) to calculate the gain required for the TLV910x-Q1 to produce the necessary output voltage is calculated using.

$$\text{Gain} = \frac{(V_{OUT_MAX} - V_{OUT_MIN})}{(V_{IN_MAX} - V_{IN_MIN})} \quad (3)$$

[Equation 3](#) calculates the required gain as 49V/V, which is set with resistors R_F and R_G . [Equation 4](#) is used to size the resistors, R_F and R_G , to set the gain of the TLV910x-Q1 to 49V/V.

$$\text{Gain} = 1 + \frac{(R_F)}{(R_G)} \quad (4)$$

With R_F as 360k Ω , [Equation 4](#) calculates R_G as 7.5k Ω . This example has the R_F and R_G as 360k Ω and 7.5k Ω because these values are the standard resistor values that create a 49:1 ratio. Other resistors that create a 49:1 ratio can also be used. [Figure 7-2](#) shows the measured transfer function of the circuit shown in [Figure 7-1](#).

7.2.1.3 Application Curve

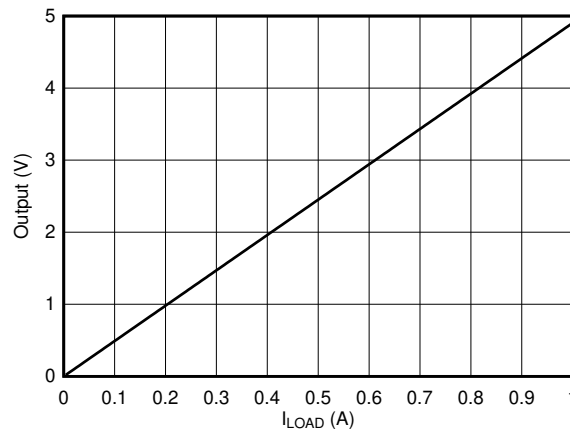


Figure 7-2. Low-Side, Current-Sense, Transfer Function

7.3 Power Supply Recommendations

The TLV910x-Q1 is specified for operation from 2.7V to 16V ($\pm 1.35V$ to $\pm 8V$), and many specifications apply from -40°C to 125°C .

CAUTION

Supply voltages larger than 20V can permanently damage the device. See [Absolute Maximum Ratings](#).

Place 0.1µF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. See [Layout](#) for more information.

7.4 Layout

7.4.1 Layout Guidelines

For best operational performance of the device, use good PCB layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and op amp. Bypass capacitors are used to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
 - Connect low-ESR, 0.1µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital and analog grounds paying attention to the flow of the ground current.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicular is much better as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. As illustrated in [Figure 7-4](#), keeping RF and RG close to the inverting input minimizes parasitic capacitance.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.
- Cleaning the PCB following board assembly is recommended for best performance.
- Any precision integrated circuit can experience performance shifts due to moisture ingress into the plastic package. Following any aqueous PCB cleaning process, baking the PCB assembly is recommended to remove moisture introduced into the device packaging during the cleaning process. A low temperature, post cleaning bake at 85°C for 30 minutes is sufficient for most circumstances.

7.4.2 Layout Example

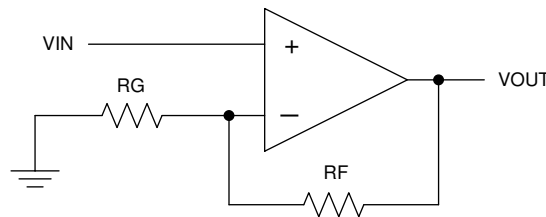


Figure 7-3. Schematic Representation

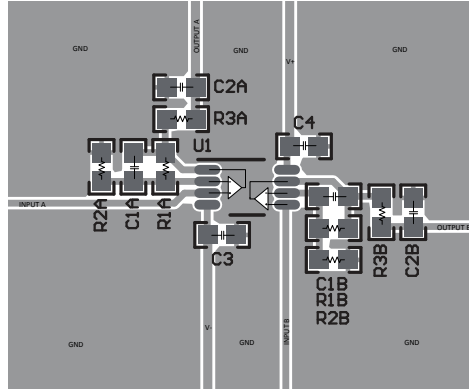


Figure 7-4. Example Layout for VSSOP-8 (DGK) Package

8 Device and Documentation Support

8.1 Device Support

8.1.1 Development Support

8.1.1.1 TINA-TI™ (Free Software Download)

TINA™ is a simple, powerful, and easy-to-use circuit simulation program based on a SPICE engine. TINA-TI is a free, fully-functional version of the TINA software, preloaded with a library of macro models in addition to a range of both passive and active models. TINA-TI provides all the conventional DC, transient, and frequency domain analysis of SPICE, as well as additional design capabilities.

Available as a [free download](#) from the Analog eLab Design Center, TINA-TI offers extensive post-processing capability that allows users to format results in a variety of ways. Virtual instruments offer the ability to select input waveforms and probe circuit nodes, voltages, and waveforms, creating a dynamic quick-start tool.

Note

These files require that either the TINA software (from DesignSoft™) or TINA-TI software be installed. Download the free TINA-TI software from the [TINA-TI folder](#).

8.2 Documentation Support

8.2.1 Related Documentation

Texas Instruments, [EMI Rejection Ratio of Operational Amplifiers application note](#)

8.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](#). Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

8.4 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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8.5 Trademarks

TINA-TI™ is a trademark of Texas Instruments, Inc and DesignSoft, Inc.

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Bluetooth® is a registered trademark of Bluetooth SIG, Inc.

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8.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.7 Glossary

[TI Glossary](#)

This glossary lists and explains terms, acronyms, and definitions.

9 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
June 2024	*	Initial Release

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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